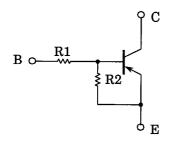
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2101F,RN2102F,RN2103F RN2104F,RN2105F,RN2106F

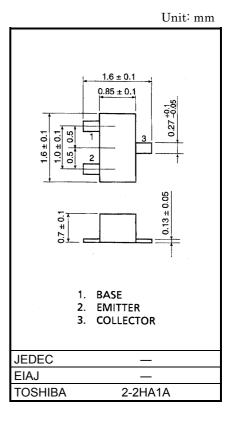
Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1101F~RN1106F

Equivalent Circuit and Bias Resister Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2101F	4.7	4.7
RN2102F	10	10
RN2103F	22	22
RN2104F	47	47
RN2105F	2.2	47
RN2106F	4.7	47



Maximum Ratings (Ta = 25°C)

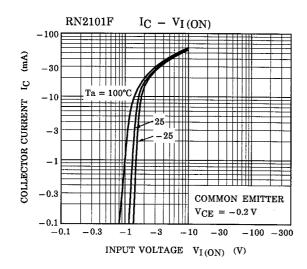
Characteris	Symbol	Rating	Unit		
Collector-base voltage	RN2101F~2106F	V_{CBO}	-50	٧	
Collector-emitter voltage	101011 - 21001	V _{CEO}	-50	V	
Emitter-base voltage	RN2101F~2104F	V _{FBO}	-10	V	
	RN2105F, 2106F	vEBO	-5		
Collector current		IC	-100	mA	
Collector power dissipation	RN2101F~2106F	PC	100	mW	
Junction temperature	RN2101F~2100F	Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

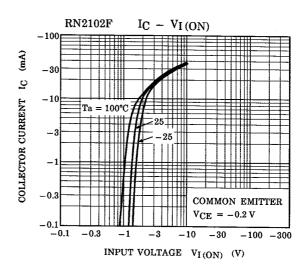


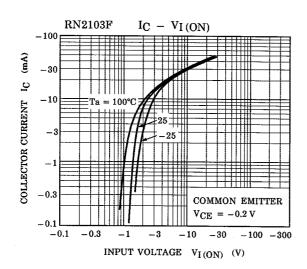
Electrical Characteristics (Ta = 25°C)

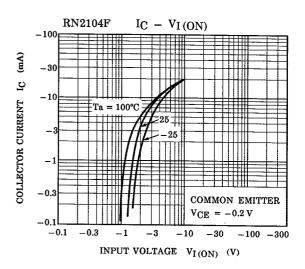
Characteristic		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN2101F	I _{CBO}		$V_{CB} = -50V, I_E = 0$	_	_	-100	A
	~2106F	I _{CEO}		V _{CE} = -50V, I _B = 0	_	_	-500	nA
	RN2101F		_	V _{EB} = -10V, I _C = 0	-0.82	_	-1.52	mA
	RN2102F	I _{EBO}			-0.38	_	-0.71	
	RN2103F				-0.17	_	-0.33	
Emitter cut-off current	RN2104F				-0.082	_	-0.15	
	RN2105F			V _{EB} = -5V, I _C = 0	-0.078	_	-0.145	
	RN2106F				-0.074	_	-0.138	
	RN2101F				30	_	_	
	RN2102F				50	_	_	
DC aumant main	RN2103F	L		V _{CE} = −5V,	70	_	_	
DC current gain	RN2104F	h _{FE}	_	I _C = -10mA	80	_	_	
	RN2105F				80	_	_	
	RN2106F				80	_	_	
Collector-emitter saturation voltage	RN2101F ~2106F	V _{CE} (sat)	_	$I_{C} = -5mA,$ $I_{B} = -0.25mA$	_	-0.1	-0.3	V
	RN2101F			V _{CE} = -0.2V, I _C = -5mA	-1.1	_	-2.0	V
Input voltage (ON)	RN2102F				-1.2	_	-2.4	
	RN2103F	V _{I (ON)} –			-1.3	_	-3.0	
	RN2104F		_		-1.5	_	-5.0	
	RN2105F				-0.6	_	-1.1	
	RN2106F				-0.7	_	-1.3	
Input voltage (OFF)	RN2101F ~2104F	V		V _{CE} = -5V, I _C = -0.1mA	-1.0	_	-1.5	V
Input voltage (OFF)	RN2105F, 2106F	V _I (OFF)	-		-0.5	_	-0.8	
Transition frequency	RN2101F ~2106F	f _T	_	V _{CE} = -10V, I _C = -5mA	_	200	_	MHz
Collector Output capacitance	RN2101F ~2106F	C _{ob}	_	V _{CB} = -10V, I _E = 0, f = 1MHz	_	3	6	pF
Input resistor	RN2101F			_	3.29	4.7	6.11	- kΩ
	RN2102F	R1 —	_		7	10	13	
	RN2103F				15.4	22	28.6	
	RN2104F				32.9	47	61.1	
	RN2105F			1.54	2.2	2.86		
	RN2106F				3.29	4.7	6.11	
Resistor ratio	RN2101F ~2104F		2 _	_	0.9	1.0	1.1	
	RN2105F	R1/R2			0.0421	0.0468	0.0515	
	RN2106F				0.09	0.1	0.11	

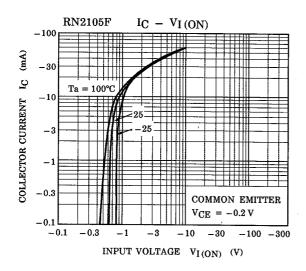
2

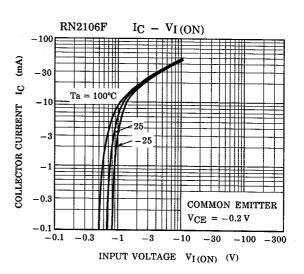




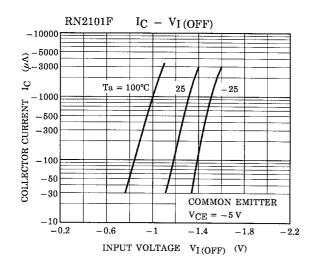


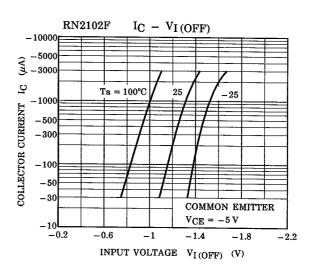


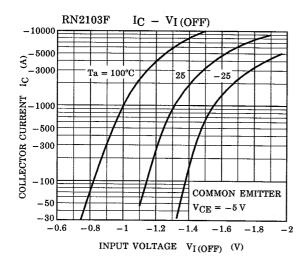


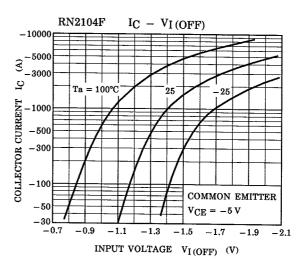


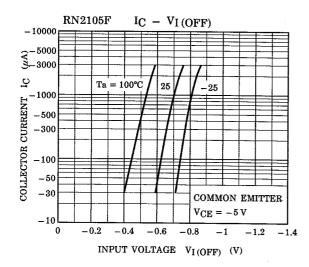
3

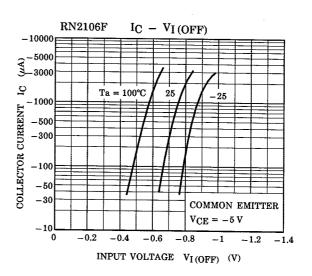


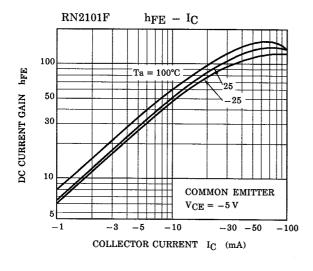


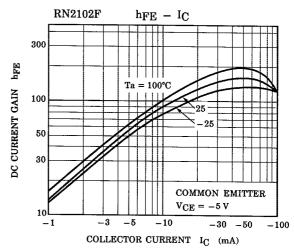


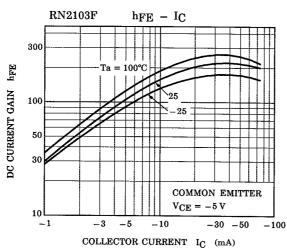


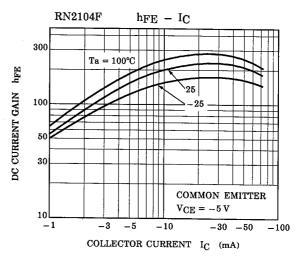


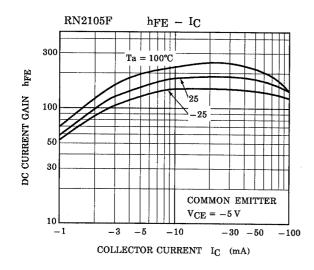


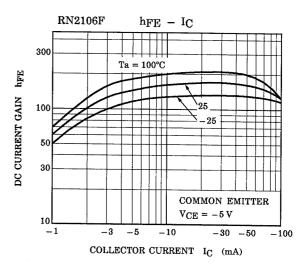




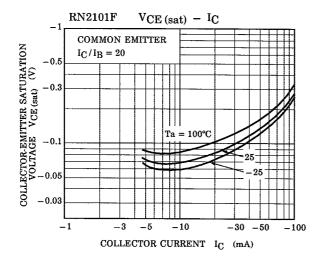


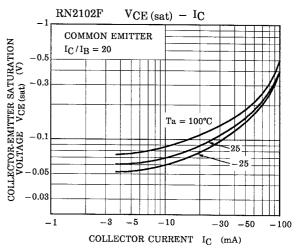


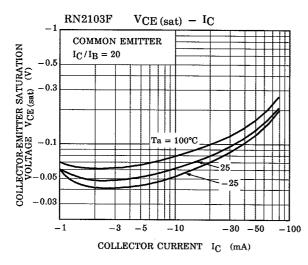


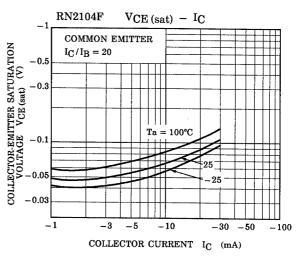


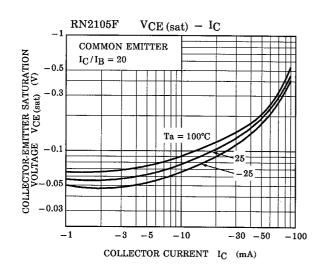
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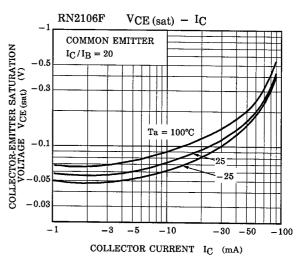












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Type Name	Marking
RN2101F	Type Name Y A
RN2102F	Type Name Y B
RN2103F	Type Name Y C
RN2104F	Type Name Y D
RN2105F	Type Name Y E
RN2106F	Type Name Y F

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